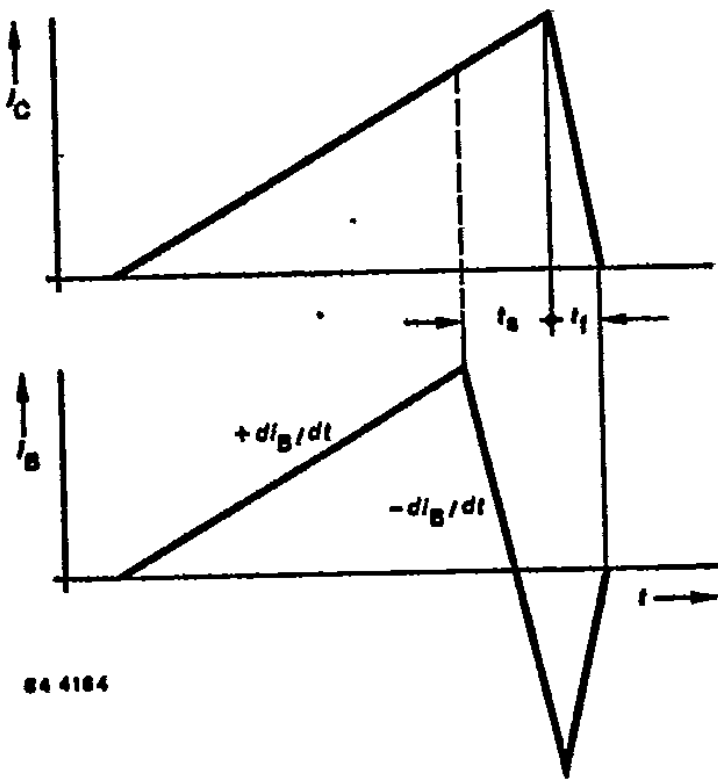
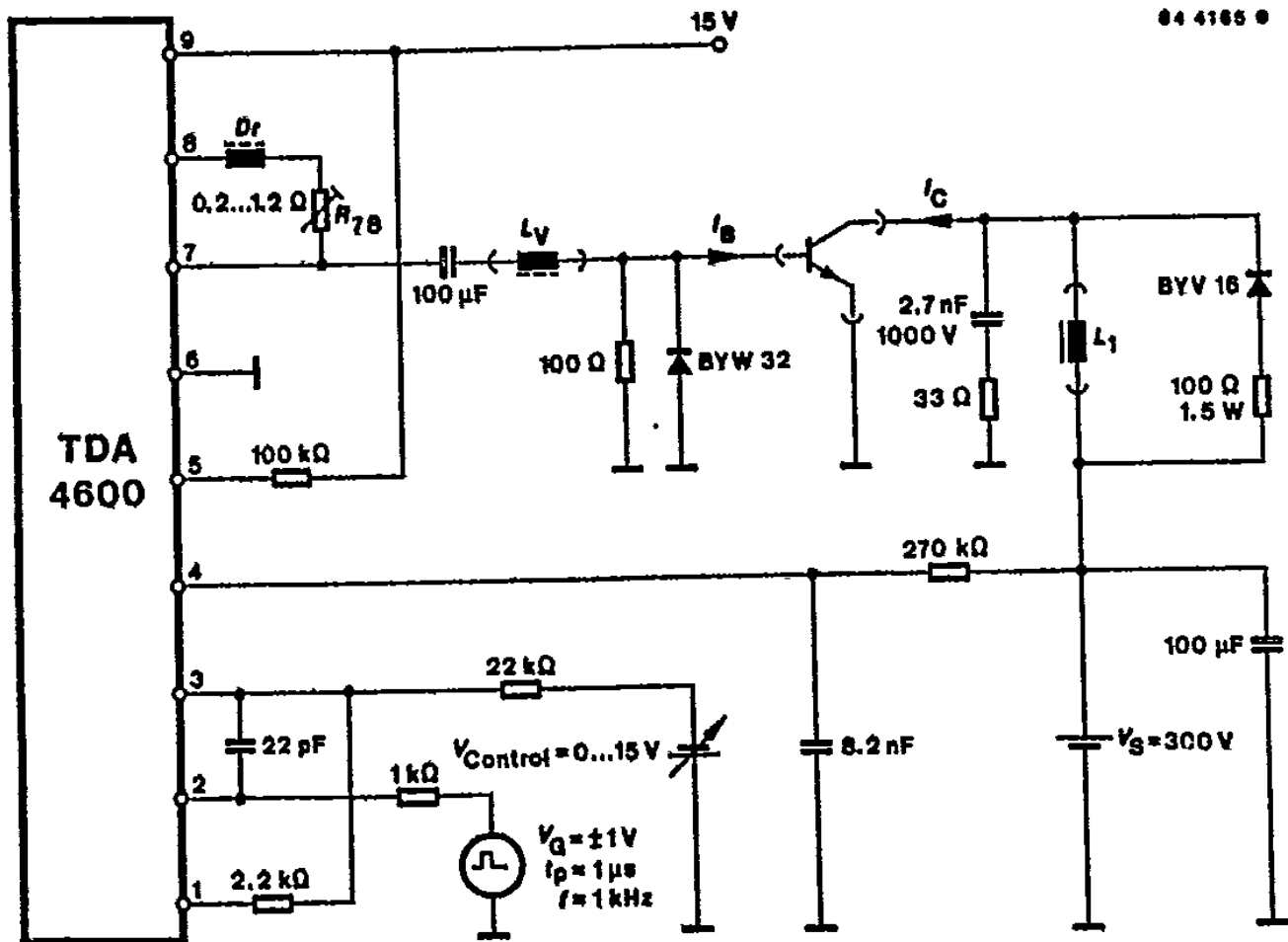


Total power dissipation				
$T_{\text{case}} \leq 25\text{ }^{\circ}\text{C}$	P_{tot}	125		W
Junction temperature	T_j	150		$^{\circ}\text{C}$
Storage temperature range	T_{stg}	-65 ... +150		$^{\circ}\text{C}$
Maximum thermal resistances				
Junction case	R_{thJC}	1.0		K/W
Characteristics				
		Min.	Typ.	Max.
$T_{\text{case}} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified				
Collector cut-off current				
$V_{\text{CE}} = 1300\text{ V}$	I_{CES}			1 mA
$T_j = 125\text{ }^{\circ}\text{C}$, $V_{\text{CE}} = 1200\text{ V}$	I_{CES}			2 mA
Collector-emitter breakdown voltage				
$I_C = 100\text{ mA}$, $L_C = 125\text{ mH}$	$V_{(\text{BR})\text{CEO}}^{1)}$	550		V
Emitter-base breakdown voltage				
$I_E = 1\text{ mA}$	$V_{(\text{BR})\text{EBO}}$	6		V
Collector saturation voltage				
$I_C = 6\text{ A}$, $I_B = 2\text{ A}$	$V_{\text{CEsat}}^{1)}$			1.8 V
Base saturation voltage				
$I_C = 6\text{ A}$, $I_B = 2\text{ A}$	$V_{\text{BEsat}}^{1)}$			2 V
DC forward current transfer ratio				
$V_{\text{CE}} = 2\text{ V}$, $I_C = 3.2\text{ A}$	h_{FE}	6		-
$V_{\text{CE}} = 5\text{ V}$, $I_C = 1.5\text{ A}$	h_{FE}	8		
$V_{\text{CE}} = 5\text{ V}$, $I_C = 10\text{ mA}$	h_{FE}	6		
$V_{\text{CE}} = 3\text{ V}$, $I_C = 4\text{ A}$	h_{FE}	5.5		
Gain bandwidth product				
$V_{\text{CE}} = 10\text{ V}$, $I_C = 500\text{ mA}$, $f = 1\text{ MHz}$	f_T		10	MHz
Switching characteristics				
$I_{\text{Cend}} = 3.2\text{ A}$, $I_{\text{Bend}} = 0.7\text{ A}$, $T_{\text{case}} = 25\text{ }^{\circ}\text{C}$, see test circuit				
Fall time	t_f			0.5 μs



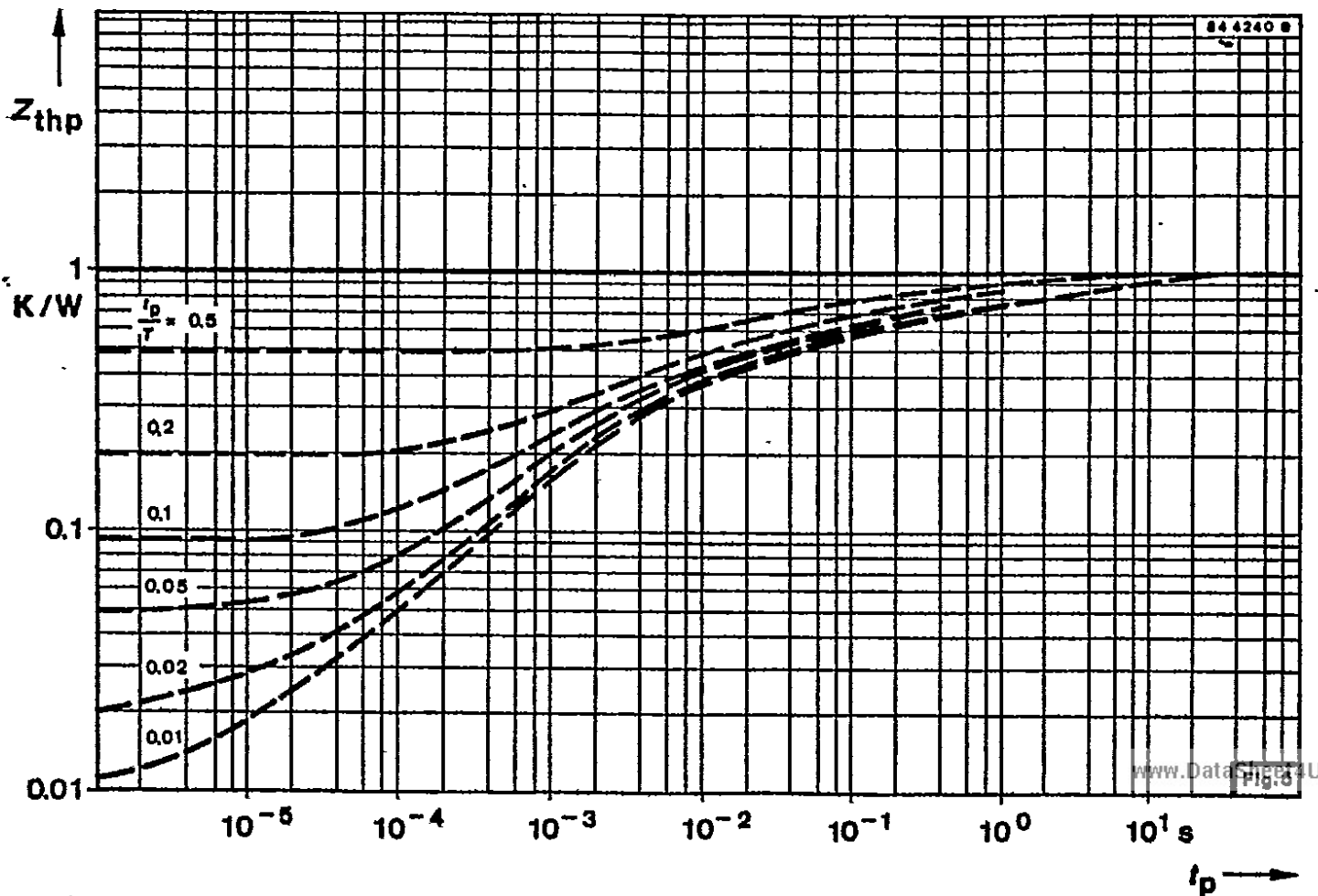
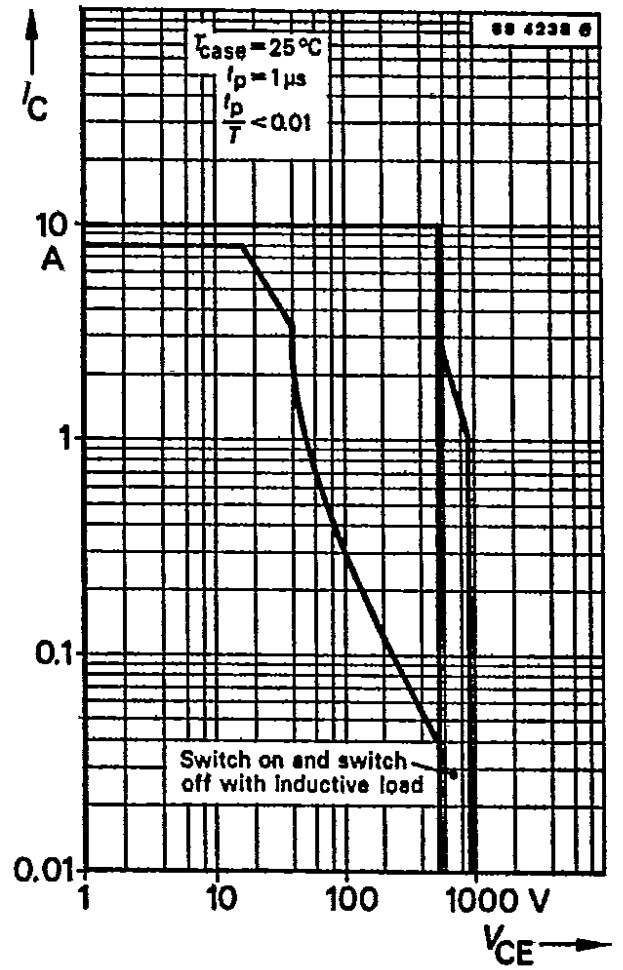
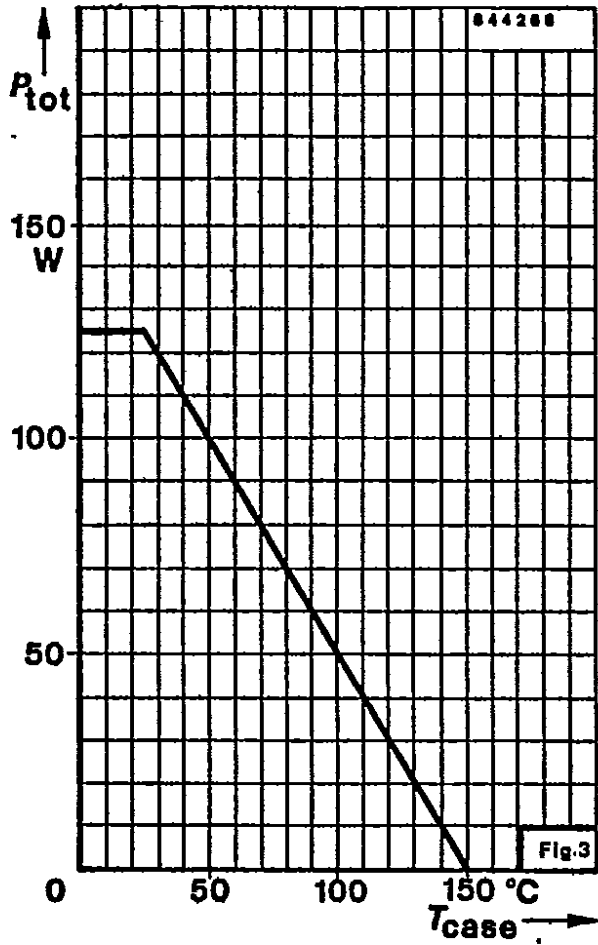
84 4184

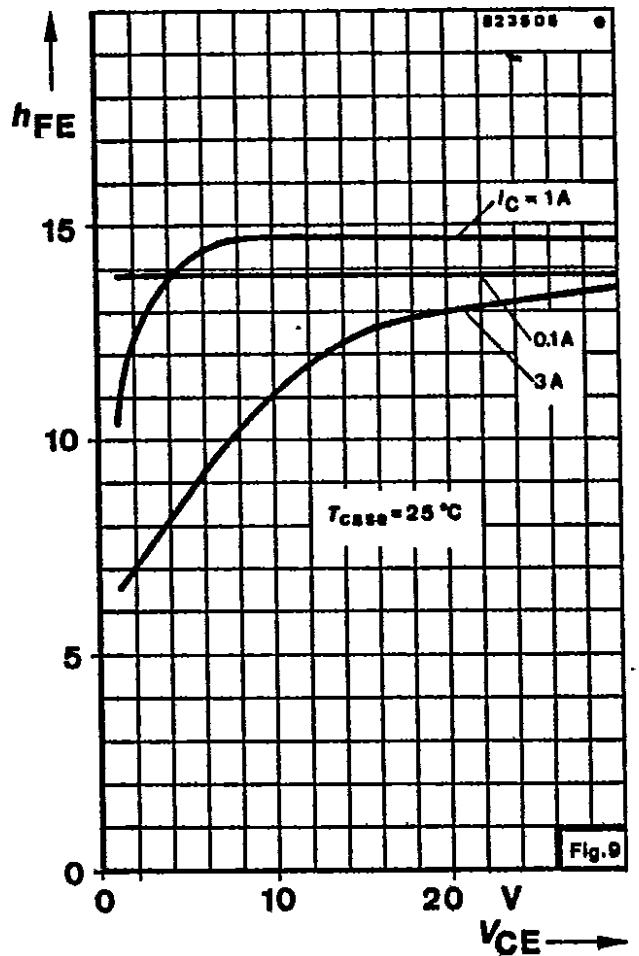
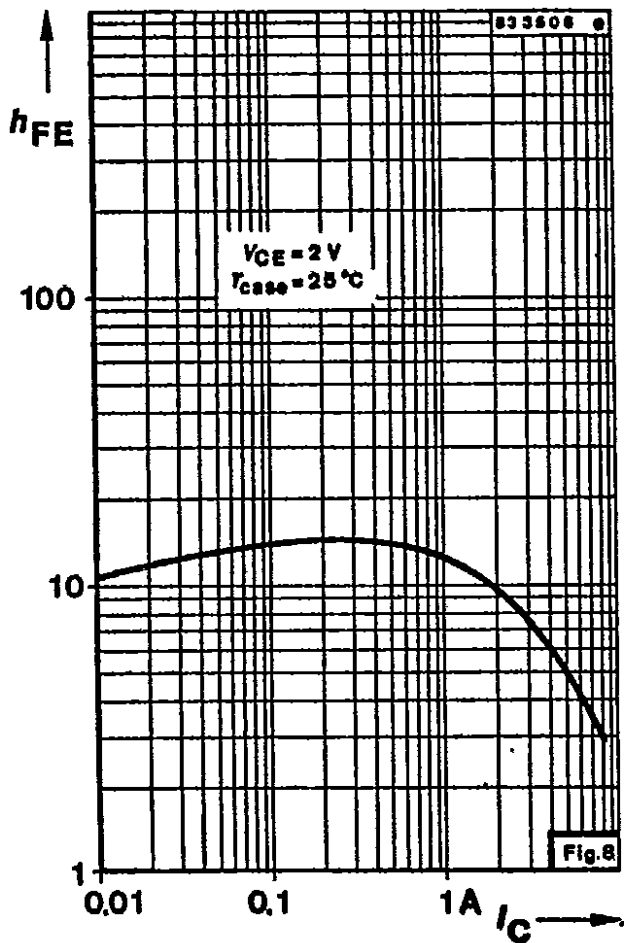
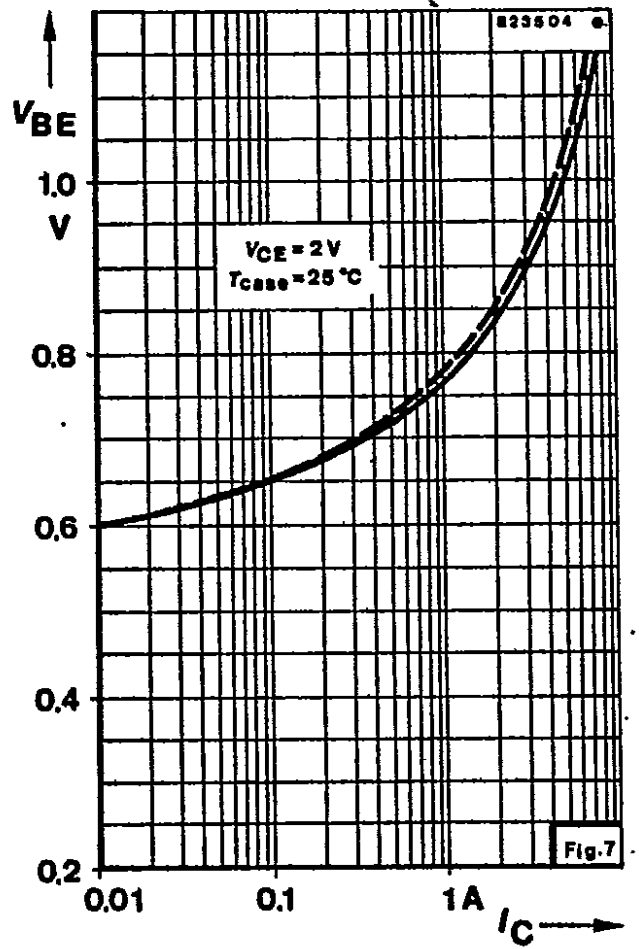
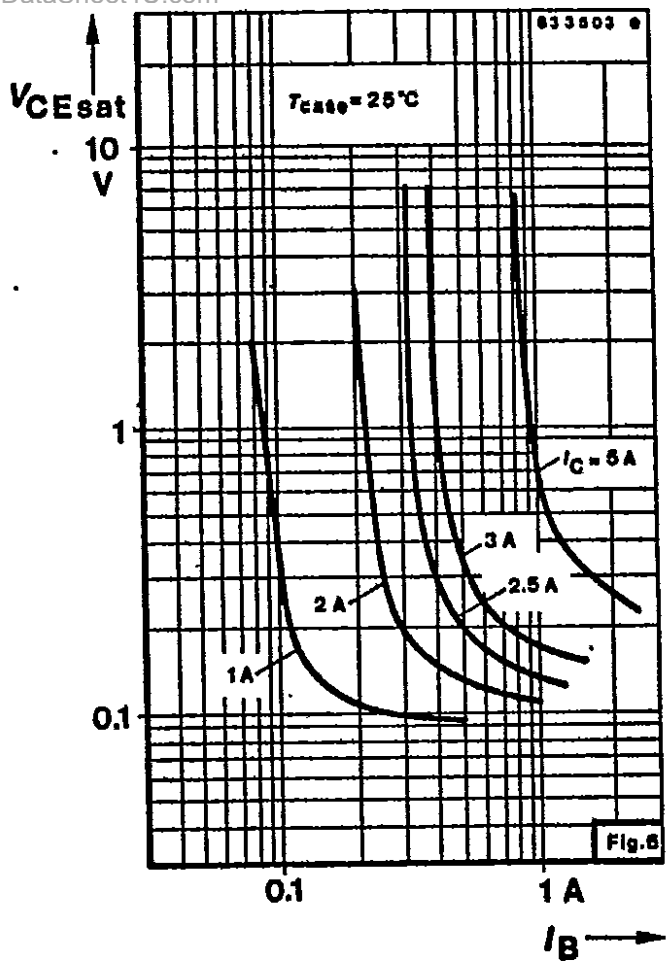
Fig. 1 Pulse diagram

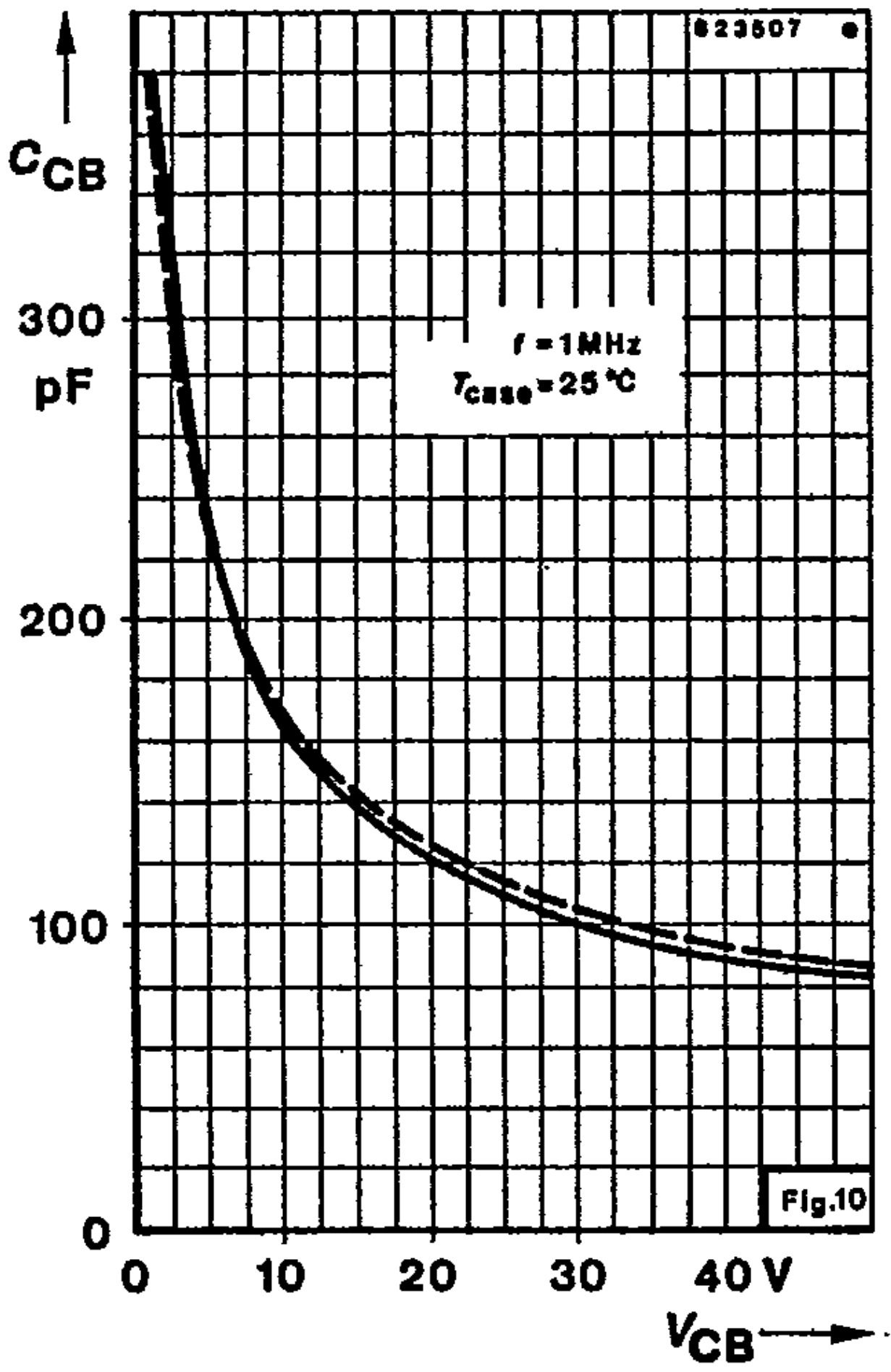


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Fig. 2 Test circuit for: t_f







● Family of curves

Besides the static (d. c.) and dynamic (a. c.) characteristics, family of curves are given for specified operating conditions. They show the typical interdependence of individual characteristics. Partly are given the scattering limits. They signify that at least 95% of the delivery lies inside these tolerances.

6.6. Additional informations

Preliminary specifications

This heading indicates that some information on the device concerned may be subject to slight changes.

Not for new developments

This heading indicates that the device concerned should not be used in equipment under development, it is, however, available for present production.

7. Taping and reeling

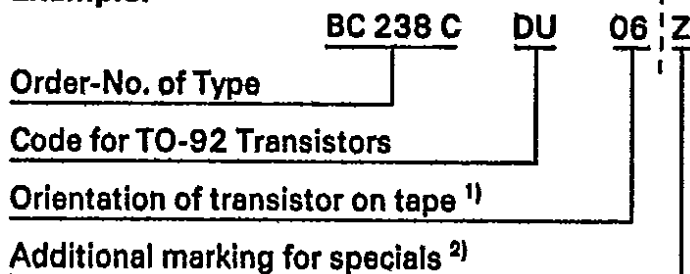
7.1. Taping of TO-92 transistors

Standard reeling: Taped on reel, reeled together with a paper film.

7.1.1. Order Numbers

Add the taping-code to the order number.

Example:



¹⁾ 06 = View on flat side of transistor, view on gummed tape

05 = View on round side of transistor, view on gummed tape

²⁾ Additional marking "0" :

Taping without paper film

Additional marking "Z":

Zigzag folded tape in special box. Marking for orientation of transistor not necessary, because box can be opened on top or bottom.

Example for order No.: BC 237 C DU Z

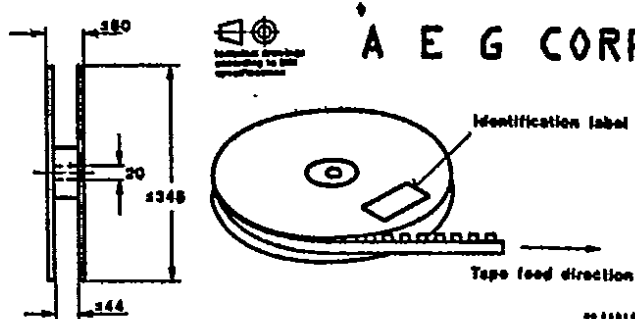


Fig. 7.1. Dimensions of reel in mm

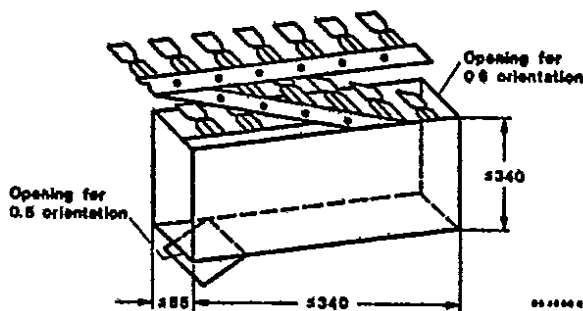


Fig. 7.2. Dimension of box for Zigzag folding in mm

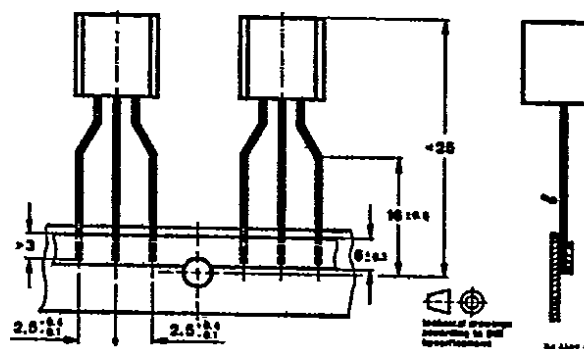


Fig. 7.3. Dimensions of tape in mm

7.1.2 Quantity of devices

1 000 devices per reel

2 000 devices per folded tape in special box.

7.2 Taped transistors in SOT 23 and SOT 143 case

a) Standard taping

Designation is attached with code GS 08 in case of standard taping. Example for normal version transistors as standard taped: BF 569-GS08.

Example for R-version transistors as standard taped: BF 569 R-GS 08.

In case of standard taping, the transistor orientation on the tape is shown in Fig. 7.4 and Fig. 7.5.

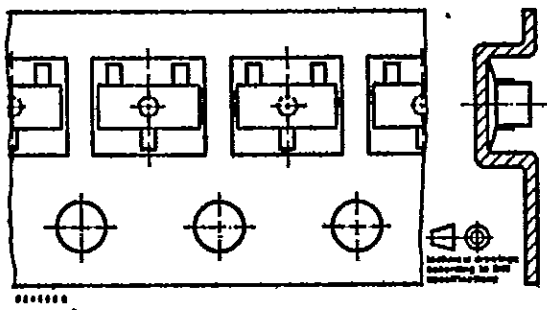


Fig. 7.4 Standard taped SOT 23

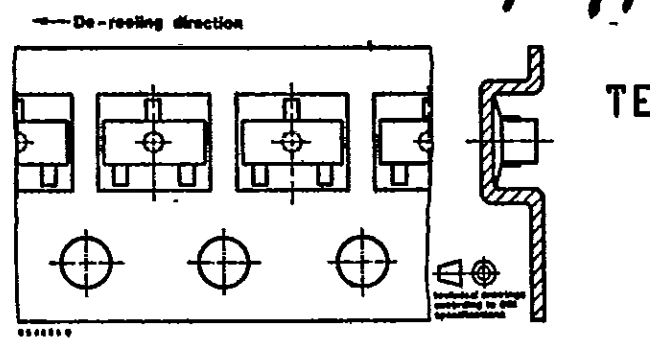


Fig. 7.6 Reverse taped SOT 23

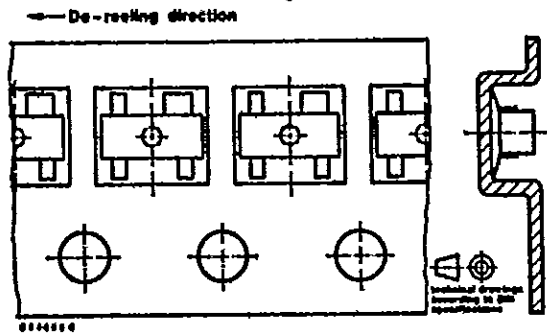


Fig. 7.5 Standard taped SOT 143

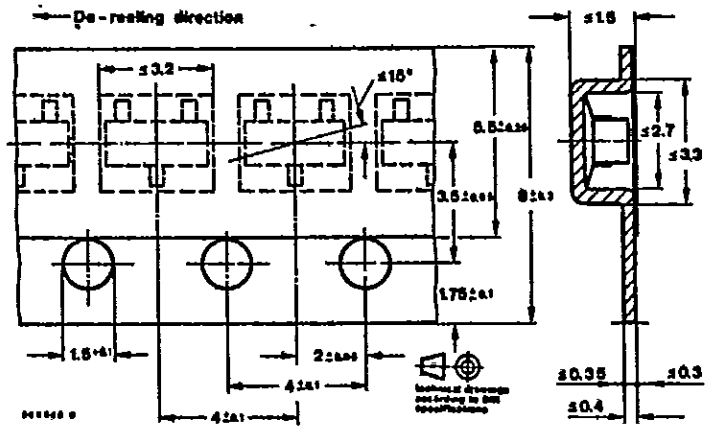


Fig. 7.7 Dimensions of tape in mm

b) Reverse taping

Designation is attached with code GS 07 in case of reverse taping. Example for normal version transistors as reverse taped: BF 569 R-GS 07. Example for R-version transistors as reverse taping: BF 569 R-GS 07.

In case of reverse taping, the transistor orientation on the tape is shown in Fig. 6. Regarding MOF-FET and MES-FET devices, reverse taping is at present not available.

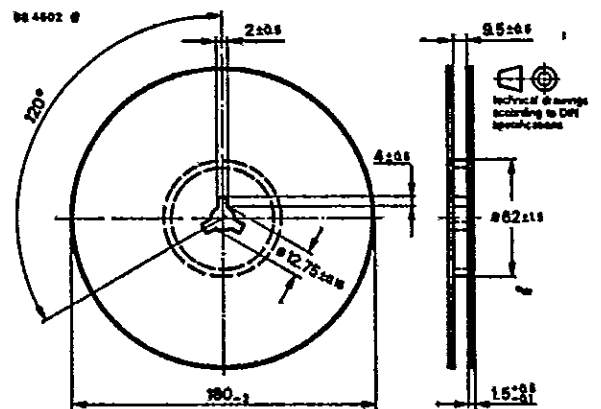


Fig. 7.8 Dimensions of reel in mm

7.2.2 Quantity of devices

3000 devices per reel

For case

12A 3 DIN 41 869
JEDEC TO 126 (SOT 32)

14A 3 DIN 41 869
JEDEC TO 220 (SOT 78)

15A 3 DIN 41 869
(TOP3) for clip mounting

15A 3 DIN 41 869
(TOP3) for screw mounting

15A 3 DIN 41 869
(TOP3)

3B 2 DIN 41 872
JEDEC TO 3

Devices with high reverse voltage

8. Accessories

Number	Fig.	Designation
119880	8.1.	Isolating washer thickness 60 µm
564542	8.2.	Isolating washer thickness 50 µm
912884	8.3	Isolating washer thickness 50 µm
191 131	8.4	Isolating washer thickness 50 µm
191 140	8.5	Mounting clip
569524	8.6	Isolating washer thickness 100 µm + 50 µm